



DMTH4005SPSQ

10V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on) Max	ID Tc = +25°C (Note 7)	
40V	$3.7 \text{m}\Omega @ \text{V}_{\text{GS}} = 10 \text{V}$	100A	

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

PowerDI5060-8





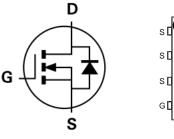
Bottom View

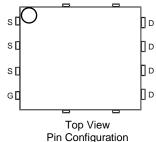
- **Features**
- Rated to +175°C Ideal For High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable And Robust End Application
- Low RDS(ON) Minimizes Power Losses
- Low Qg Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4005SPSQ is suitable for automotive applications requiring specific change control: this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.097 grams (Approximate)





Internal Schematic

Ordering Information (Note 4)

Part Number	Packaga	Packing		
	Package	Qty.	Carrier	
DMTH4005SPSQ-13	PowerDI5060-8	2,500	Tape & Reel	

Pin1

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



) | | = Manufacturer's Marking H4005SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 24 = 2024)WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	Vdss	40	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 5)	T _A = +25°C T _A = +70°C	ID	20.9 17.5	А
Continuous Drain Current (Notes 6 & 7)	Tc = +25°C Tc = +100°C	ID	100 100	А
Maximum Continuous Body Diode Forward Current (Note 6)	ls	100	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	ldм	150	A	
Avalanche Current, L=0.6mH	I _{AS}	21	A	
Avalanche Energy, L=0.6mH		Eas	132.3	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{0JA}	57	°C/W
Total Power Dissipation (Note 6)	PD	150	W	
Thermal Resistance, Junction to Case (Note 6)		Rejc	1	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

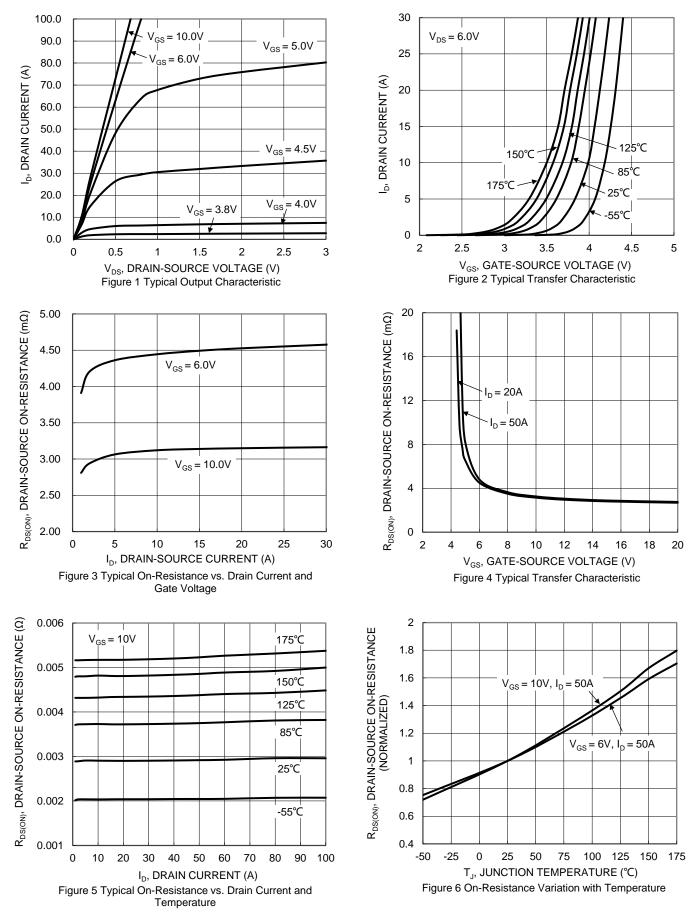
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)			1			
Drain-Source Breakdown Voltage	BVDSS	40	—	_	V	$V_{GS} = 0V, I_D = 1mA$
Zero Gate Voltage Drain Current	IDSS	_	—	1	μA	$V_{DS} = 32V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	2.9	3.7	mΩ	$V_{GS} = 10V, I_D = 50A$
Diode Forward Voltage	Vsd		0.88		V	$V_{GS} = 0V$, $I_S = 50A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss		3,062	_		$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz
Output Capacitance	Coss		902.2	_	pF	
Reverse Transfer Capacitance	Crss	_	179.2			
Gate Resistance	Rg		0.67	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qg	_	49.1			V _{DD} = 20V, I _D = 50A, V _{GS} = 10V
Gate-Source Charge	Qgs		10.3	_	nC	
Gate-Drain Charge	Q _{gd}	_	13	—		
Turn-On Delay Time	tD(ON)	_	8.7			$V_{DD} = 20V, V_{GS} = 10V,$ $I_D = 50A, R_G = 3\Omega$
Turn-On Rise Time	tR		6.8	_	-	
Turn-Off Delay Time	t _{D(OFF)}		18.6		ns	
Turn-Off Fall Time	tF		7.3			
Body Diode Reverse Recovery Time	t _{RR}	_	31.8	_	ns	I _F = 50A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	_	26.5		nC	$T_{\rm F} = 50$ A, $u/ut = 100$ A/µS

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).
Package limited.
Short duration pulse test used to article in a first strategy for the exposed drain pad. Notes:

8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.



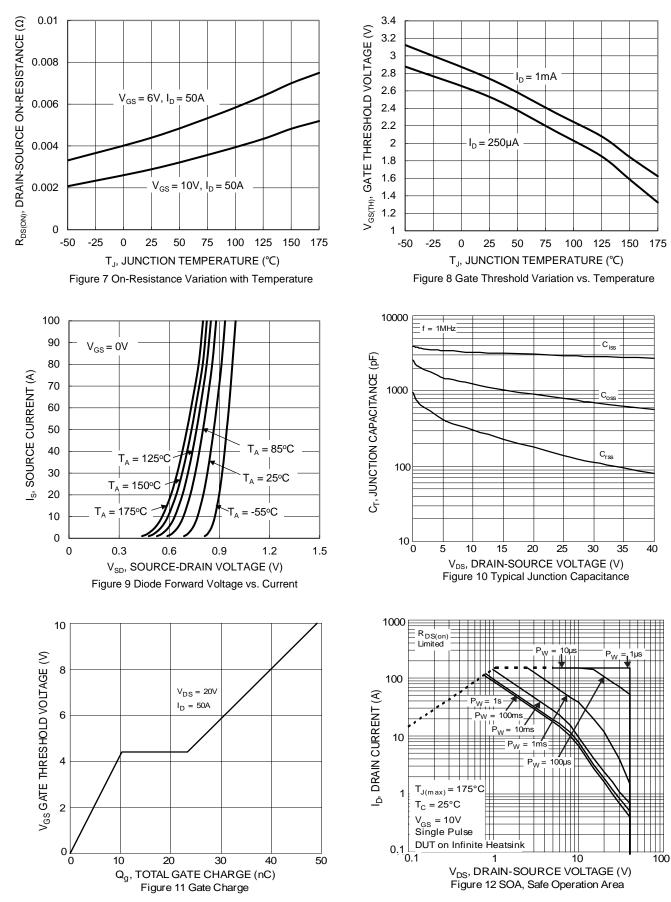
DMTH4005SPSQ



DMTH4005SPSQ Document number: DS38159 Rev. 3 - 2

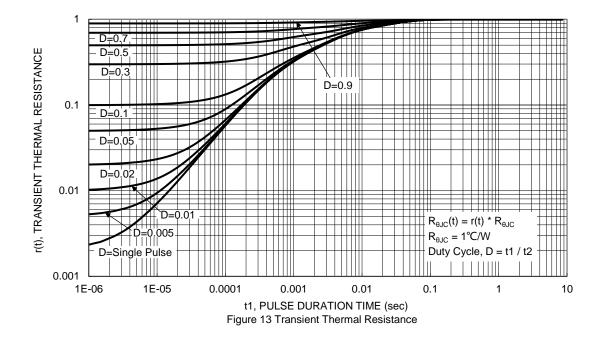


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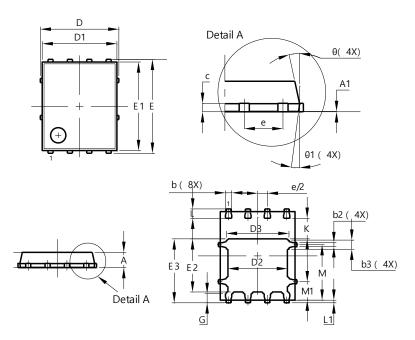






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

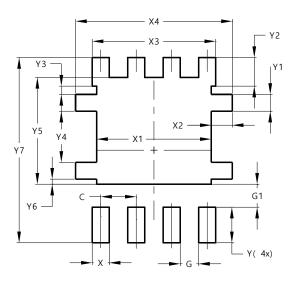


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
c	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC	;		
G	0.51	0.71	0.61		
κ	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
Μ	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

PowerDI5060-8



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